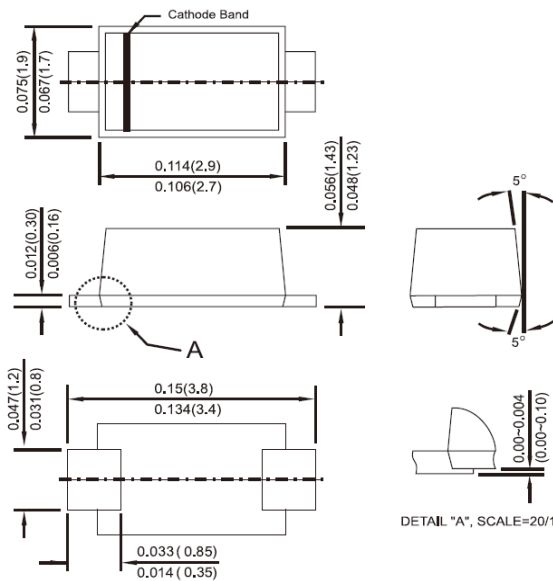


Sub SMA

**RoHS
COMPLIANCE**

Features

- ✧ For surface mounted application
- ✧ Low profile package
- ✧ Low power loss, high efficiency
- ✧ Ideal for automated placement
- ✧ Glass passivated chip junction
- ✧ High temperature soldering:
260°C/10 seconds at terminals
- ✧ Green compound with suffix "G" on packing code & prefix "G" on datecode


Mechanical Data

- ✧ Case: Sub SMA plastic case
- ✧ Terminal: Pure tin plated, lead free
- ✧ Polarity: Color band cathode end
- ✧ Packing: 8mm/12mm tape per EIA STD RS-481
- ✧ Weight: 0.0196 grams

Dimensions in inches and (millimeters)
Marking Diagram


- EXL = Specific Device Code
- G = Green Compound
- Y = Year
- M = Work Month

Maximum Ratings and Electrical Characteristics

Rating at 25 °C ambient temperature unless otherwise specified.

Single phase, half wave, 60 Hz, resistive or inductive load.

For capacitive load, derate current by 20%

Type Number	Symbol	ES 1AL	ES 1BL	ES 1CL	ES 1DL	ES 1FL	ES 1GL	ES 1HL	ES 1JL	Unit	
Maximum Repetitive Peak Reverse Voltage	V_{RRM}	50	100	150	200	300	400	500	600	V	
Maximum RMS Voltage	V_{RMS}	35	70	105	140	210	280	350	420	V	
Maximum DC Blocking Voltage	V_{DC}	50	100	150	200	300	400	500	600	V	
Maximum Average Forward Rectified Current	$I_{F(AV)}$	1								A	
Peak Forward Surge Current, 8.3 ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	I_{FSM}	30								A	
Maximum Instantaneous Forward Voltage (Note 1) @ 1 A	V_F	0.95			1.3		1.7			V	
Maximum Reverse Current @ Rated VR $T_A=25\text{ }^\circ\text{C}$ $T_A=125\text{ }^\circ\text{C}$	I_R	5 100								uA	
Maximum Reverse Recovery Time (Note 2)	T_{rr}	35								nS	
Typical Junction Capacitance (Note 3)	C_j	10			8						pF
Typical Thermal Resistance	$R_{\theta JA}$ $R_{\theta JL}$	85 35								°C/W	
Operating Temperature Range	T_J	- 55 to + 150								°C	
Storage Temperature Range	T_{STG}	- 55 to + 150								°C	

Note 1: Pulse Test with PW=300 usec, 1% Duty Cycle

 Note 2: Reverse Recovery Test Conditions: $I_F=0.5A$, $I_R=1.0A$, $I_{RR}=0.25A$

Note 3: Measured at 1 MHz and Applied Reverse Voltage of 4.0V D.C.

RATINGS AND CHARACTERISTIC CURVES (ES1AL THRU ES1JL)

FIG.1 FORWARD CURRENT DERATING CURVE

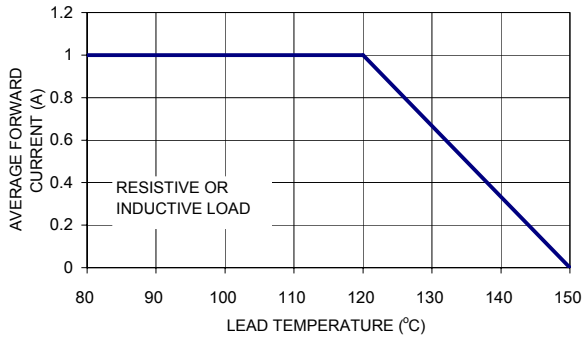


FIG. 2 TYPICAL FORWARD CHARACTERISTICS

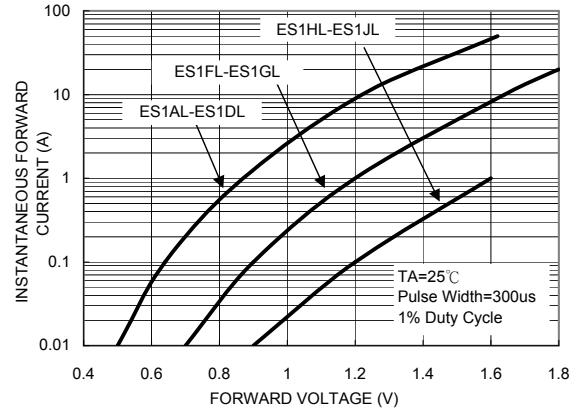


FIG. 3 MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

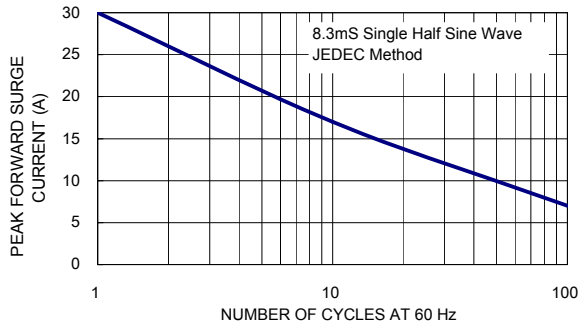


FIG. 4 TYPICAL JUNCTION CAPACITANCE

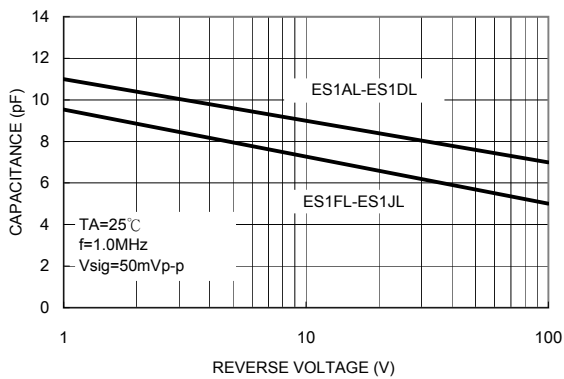


FIG. 5 TYPICAL REVERSE CHARACTERISTICS

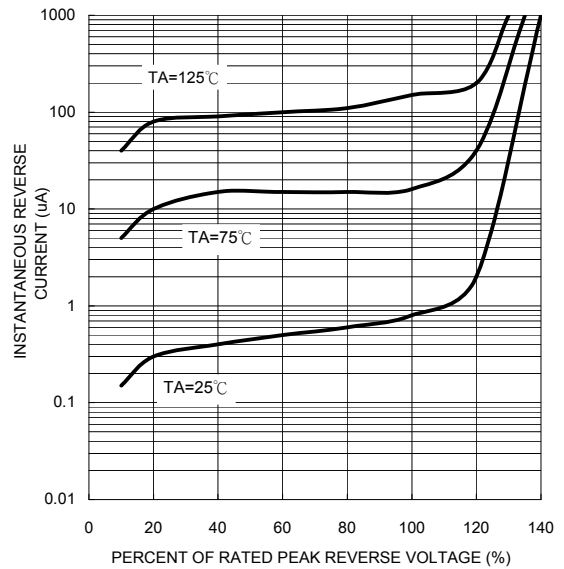


FIG.6- REVERSE RECOVERY TIME CHARACTERISTIC AND TEST CIRCUIT DIAGRAM

